

Silicon PNP Power Transistors

2SB555 2SB556

DESCRIPTION

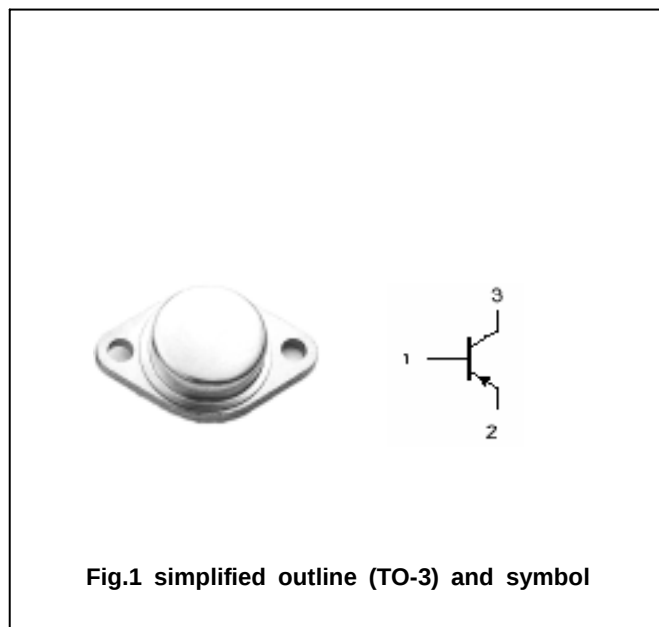
- With TO-3 package
- Complement to type 2SD425/426
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SB555	Open emitter	-140	V
		2SB556		-120	
V_{CEO}	Collector-emitter voltage	2SB555	Open base	-140	V
		2SB556		-120	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-12	A
I_E	Emitter current			12	A
P_C	Collector power dissipation		$T_C=25$	100	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~150	

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CHARACTERISTICS

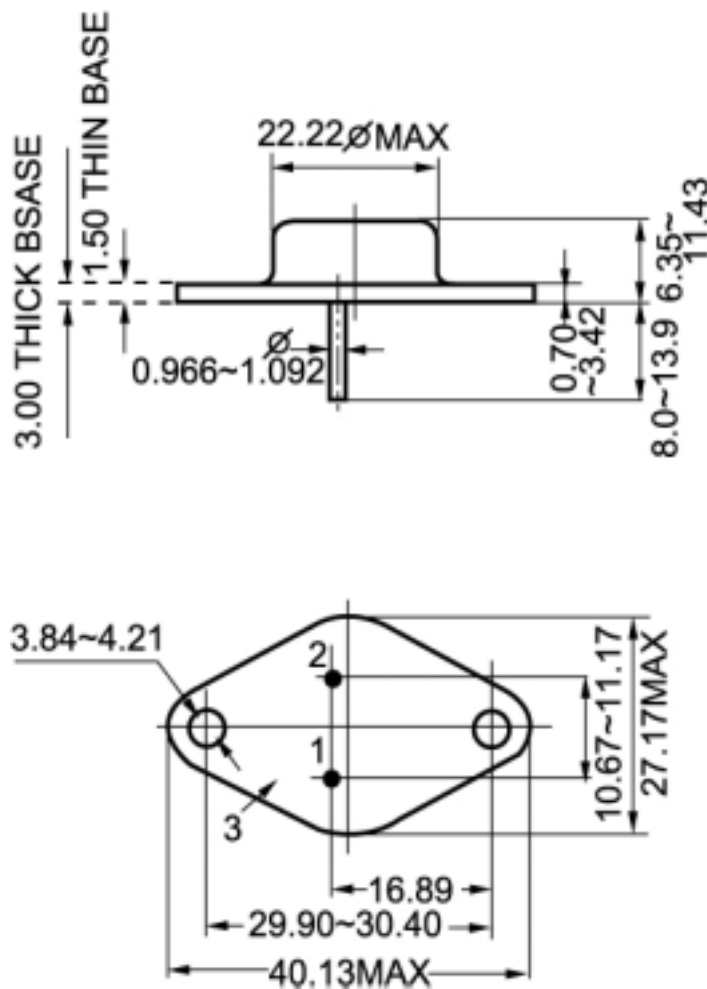
T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB555	I _C =-0.1A ; I _B =0	-140			V
		2SB556		-120			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-10mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	2SB555	I _C =-7A; I _B =-0.7A			-3.0	V
		2SB556	I _C =-6A; I _B =-0.6A				
V _{BE}	Base-emitter on voltage		I _C =-7A ; V _{CE} =-5V			-2.5	V
I _{CBO}	Collector cut-off current		V _{CB} =-50V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE}	DC current gain		I _C =-2A ; V _{CE} =-5V	40		140	
C _{OB}	Output capacitance		I _E =0 ; V _{CB} =-10V; f=1.0MHz		330		pF
f _T	Transition frequency		I _C =-2A ; V _{CE} =-5V		6		MHz

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)